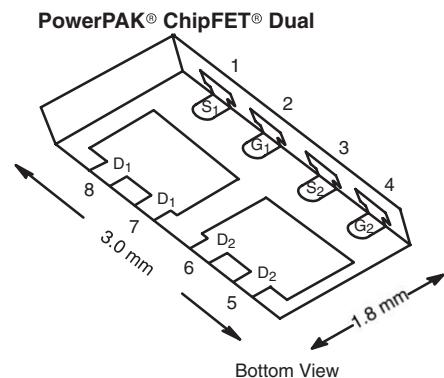


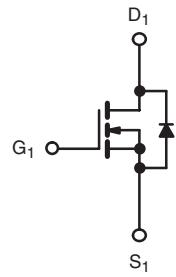
N- and P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
N-Channel	20	0.036 at V _{GS} = 4.5 V	6.0	5.4 nC
		0.063 at V _{GS} = 2.5 V	6.0	
P-Channel	- 20	0.064 at V _{GS} = - 4.5 V	- 6.0	6.0 nC
		0.095 at V _{GS} = - 2.5 V	- 6.0	

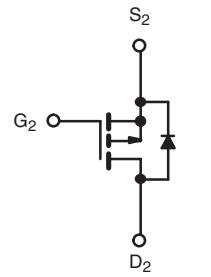


Marking Code

 Part # Code
 Lot Traceability and Date Code



N-Channel MOSFET



P-Channel MOSFET

Ordering Information: Si5519DU-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V _{DS}	20	- 20	V
Gate-Source Voltage	V _{GS}	± 12		
Continuous Drain Current (T _J = 150 °C)	I _D	6.0 ^a	- 6.0 ^a	A
		6.0 ^a	- 6.0 ^a	
		6.0 ^{a, b, c}	- 4.8 ^{b, c}	
		4.9 ^{b, c}	- 3.8 ^{b, c}	
Pulsed Drain Current	I _{DM}	25	- 20	
Source Drain Current Diode Current	I _S	6.0 ^a	- 6.0 ^a	
		1.9 ^{b, c}	- 1.9 ^{b, c}	
Maximum Power Dissipation	P _D	10.4	10.4	W
		6.6	6.6	
		2.27 ^{b, c}	2.27 ^{b, c}	
		1.45 ^{b, c}	1.45 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	N-Channel		P-Channel		Unit
		Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	43	55	43	55
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	9.5	12	9.5	12

Notes:

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. See Reliability Manual for profile. The PowerPAK ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 105 °C/W.



RoHS
COMPLIANT

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

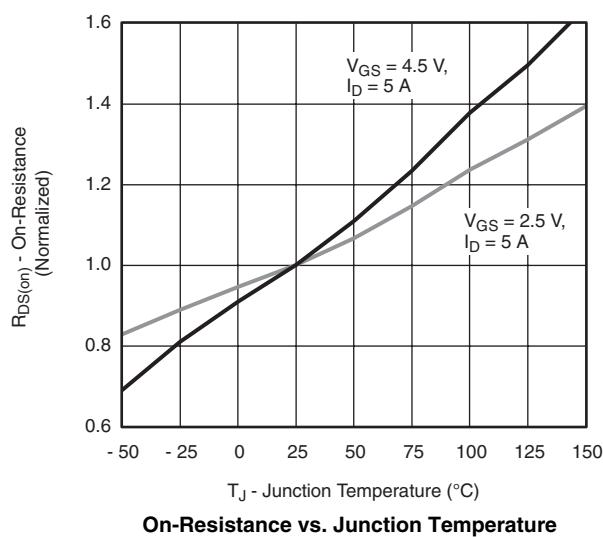
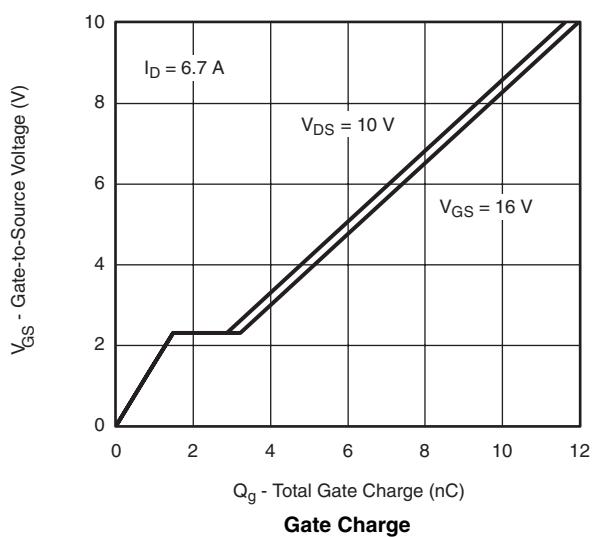
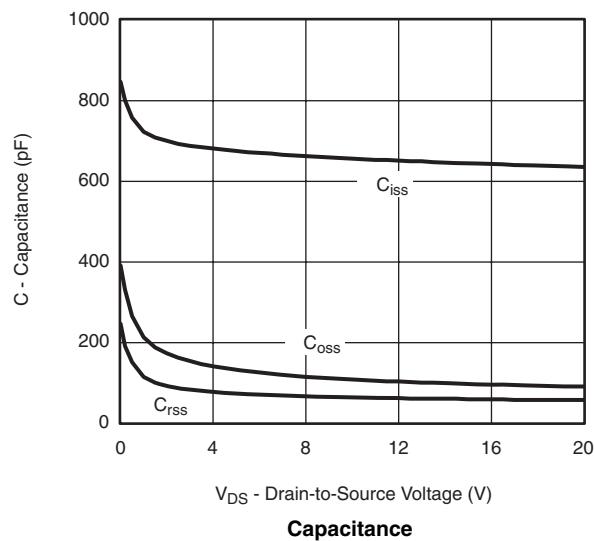
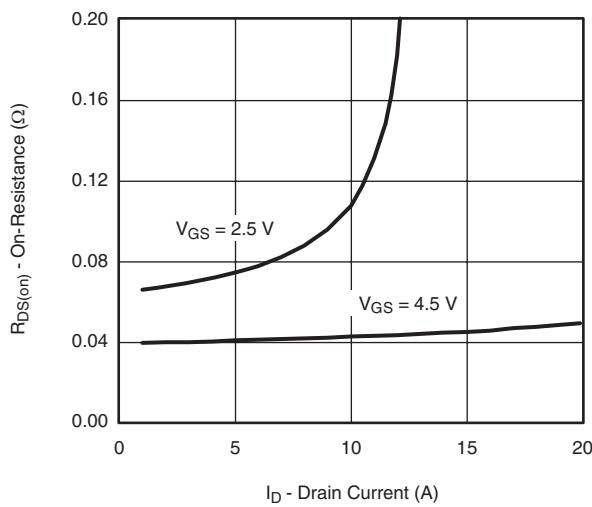
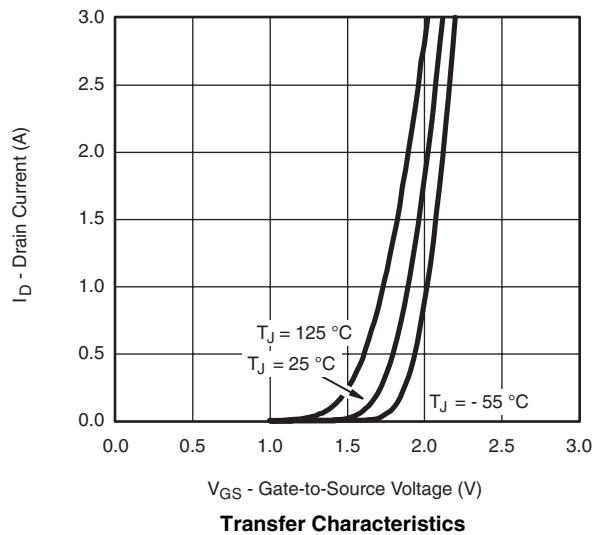
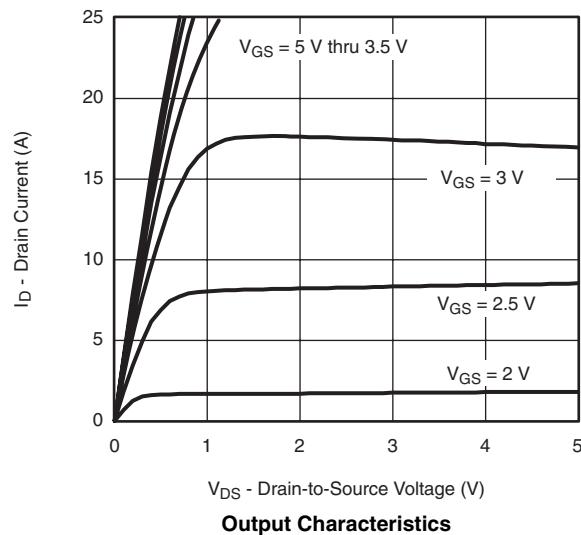
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	N-Ch	20		V	
		$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	P-Ch	- 20			
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$	N-Ch	20.74		$\text{mV}/^\circ\text{C}$	
		$I_D = -250 \mu\text{A}$	P-Ch	- 18.2			
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$	$I_D = 250 \mu\text{A}$	N-Ch	4.0			
		$I_D = -250 \mu\text{A}$	P-Ch	1.83			
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	N-Ch	0.6	1.8	V	
		$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	P-Ch	- 0.6	- 1.8		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$	N-Ch		100	nA	
			P-Ch		- 100		
Zero Gate Voltage Drain Current ^b	I_{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	N-Ch		1	μA	
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$	P-Ch		- 1		
		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$	N-Ch		10		
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$	P-Ch		- 10		
On-State Drain Current ^b	$I_{D(\text{on})}$	$V_{DS} \leq 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	N-Ch	25		A	
		$V_{DS} \leq -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	P-Ch	- 10			
Drain-Source On-State Resistance ^b	$R_{DS(\text{on})}$	$V_{GS} = 4.5 \text{ V}, I_D = 6.1 \text{ A}$	N-Ch		0.030	Ω	
		$V_{GS} = -4.5 \text{ V}, I_D = -4.8 \text{ A}$	P-Ch		0.053		
		$V_{GS} = 2.5 \text{ V}, I_D = 1.6 \text{ A}$	N-Ch		0.052		
		$V_{GS} = -2.5 \text{ V}, I_D = -1.05 \text{ A}$	P-Ch		0.078		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 10 \text{ V}, I_D = 6.7 \text{ A}$	N-Ch		15	S	
		$V_{DS} = -10 \text{ V}, I_D = -4.8 \text{ A}$	P-Ch		9.5		
Dynamic^a							
Input Capacitance	C_{iss}	N-Channel $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ P-Channel $V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	N-Ch	660		pF	
			P-Ch	475			
Output Capacitance	C_{oss}		N-Ch	108			
			P-Ch	135			
Reverse Transfer Capacitance	C_{rss}		N-Ch	65			
			P-Ch	100			
Total Gate Charge	Q_g	$V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 4.8 \text{ A}$	N-Ch	11.65	17.5	nC	
		$V_{DS} = -10 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -3.2 \text{ A}$	P-Ch	11.7	18		
Gate-Source Charge	Q_{gs}	N-Channel $V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 4.8 \text{ A}$ P-Channel $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -3.2 \text{ A}$	N-Ch	5.4	8.1		
			P-Ch	6.0	9.0		
			N-Ch	1.48			
			P-Ch	1.05			
Gate-Drain Charge	Q_{gd}		N-Ch	1.4			
			P-Ch	2.1			
Gate Resistance	R_g	$f = 1 \text{ MHz}$	N-Ch	5.2		Ω	
			P-Ch	9.8			

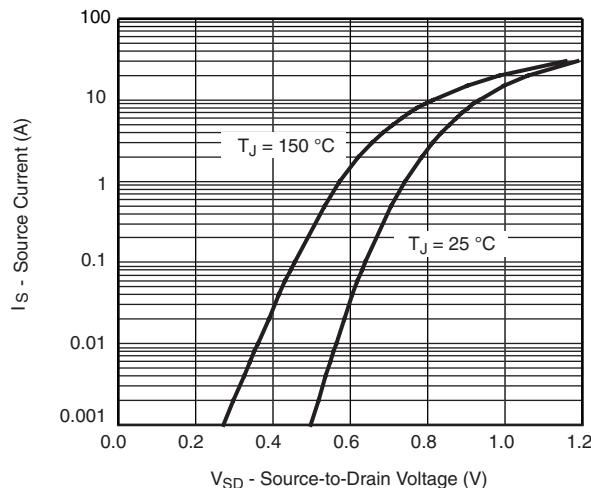
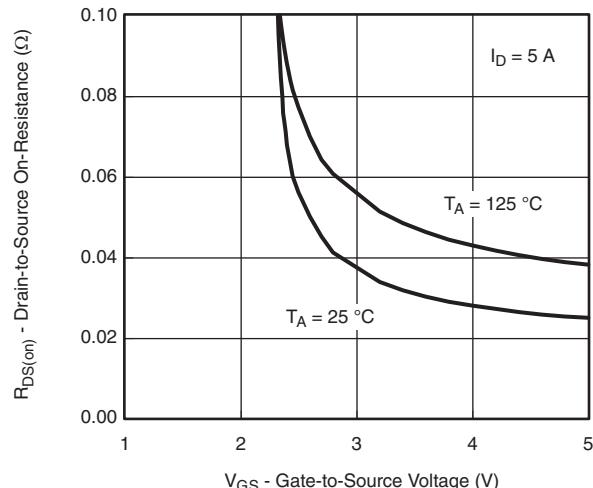
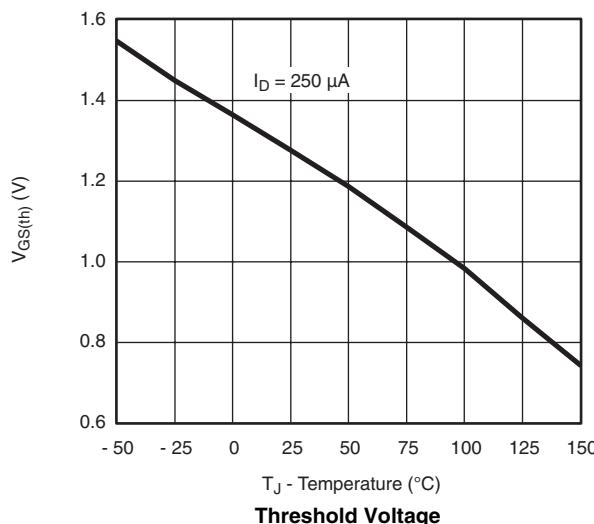
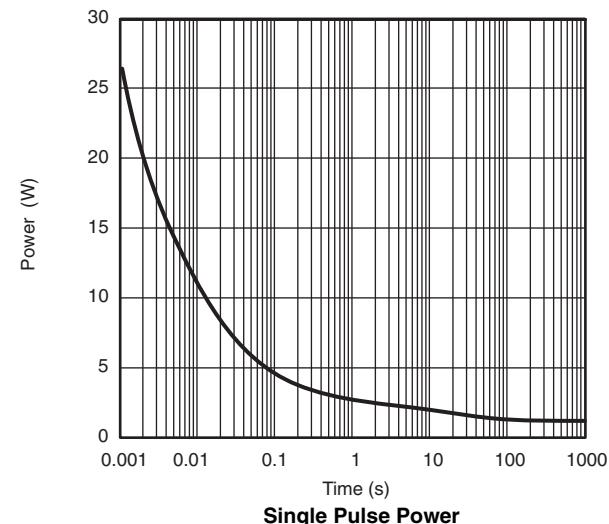
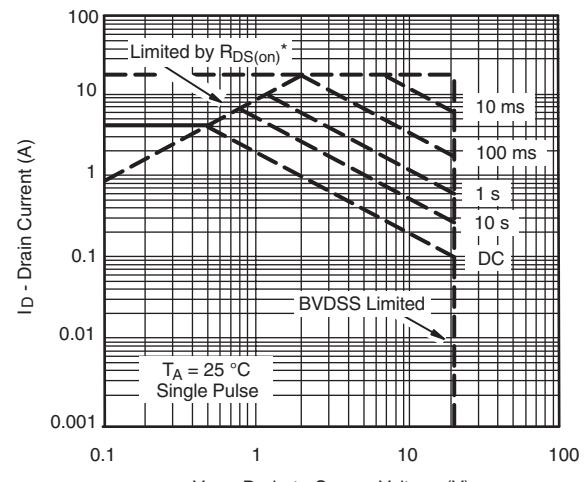
SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions			Min.	Typ. ^a	Max.
Dynamic^a							
Turn-On Delay Time	$t_{d(\text{on})}$	N-Channel $V_{DD} = 10\text{ V}$, $R_L = 2.04\ \Omega$ $I_D \cong 4.9\text{ A}$, $V_{\text{GEN}} = 4.5\text{ V}$, $R_g = 1\ \Omega$ P-Channel $V_{DD} = -10\text{ V}$, $R_L = 2.63\ \Omega$ $I_D \cong -3.8\text{ A}$, $V_{\text{GEN}} = -4.5\text{ V}$, $R_g = 1\ \Omega$	N-Ch	5.5	8.25	ns	
Rise Time	t_r		P-Ch	4.5	6.8		
Turn-Off Delay Time	$t_{d(\text{off})}$		N-Ch	15	22.5		
Fall Time	t_f		P-Ch	11	16.5		
			N-Ch	22	33		
			P-Ch	25	37.5		
			N-Ch	6	9		
			P-Ch	8.5	12.8		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$ $I_S = 3.1\text{ A}$, $V_{GS} = 0\text{ V}$ $I_S = -2.2\text{ A}$, $V_{GS} = 0\text{ V}$	N-Ch		8.6	A	
Pulse Diode Forward Current ^a	I_{SM}		P-Ch		-8.6		
Body Diode Voltage	V_{SD}		N-Ch		25		
Body Diode Reverse Recovery Time	t_{rr}		P-Ch		-20		
Body Diode Reverse Recovery Charge	Q_{rr}		N-Ch	0.8	1.2	V	
Reverse Recovery Fall Time	t_a		P-Ch	-0.8	-1.2		
Reverse Recovery Rise Time	t_b		N-Ch	14.4	21.6		
			P-Ch	20.6	31		
		$I_F = 3.1\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$ N-Channel $I_F = -2.2\text{ A}$, $dI/dt = -100\text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$	N-Ch	8	12	nC	
			P-Ch	7.2	11		
			N-Ch	10			
			P-Ch	6.6			
			N-Ch	4.4			
			P-Ch	14			

Notes:

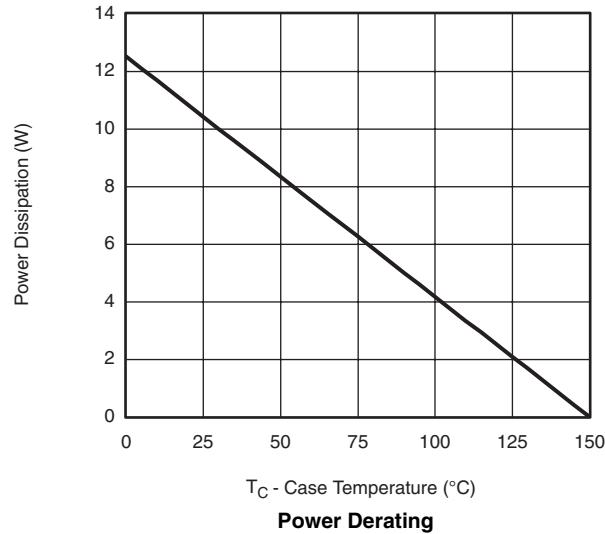
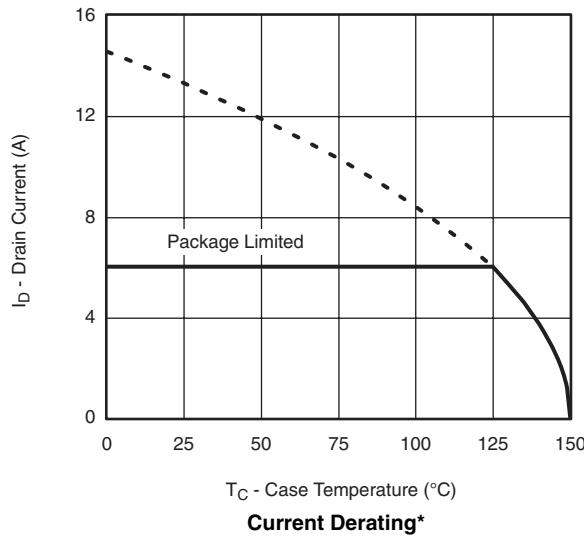
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

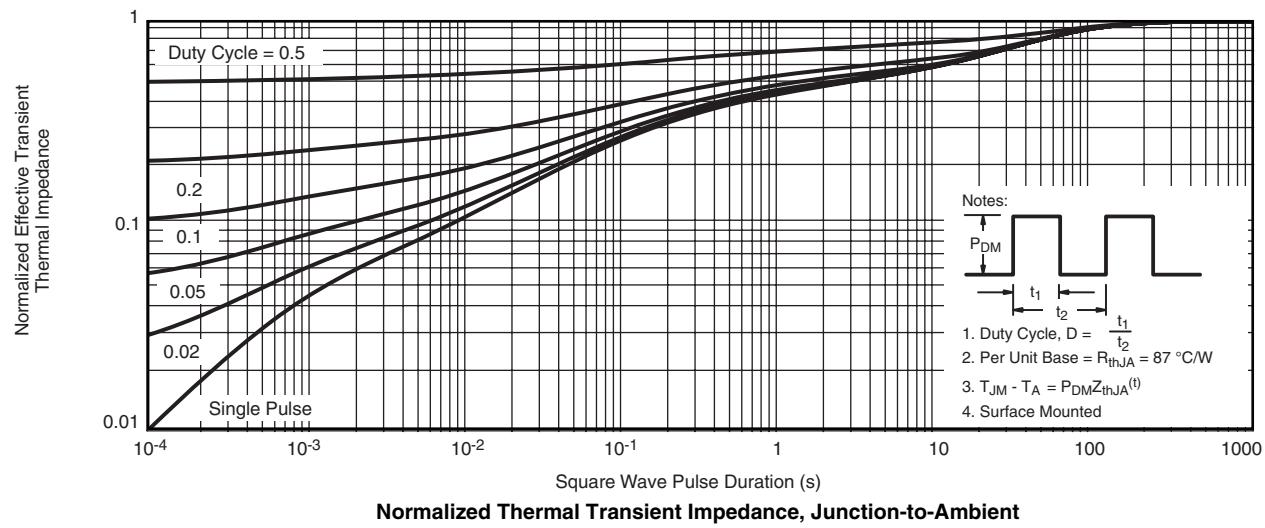
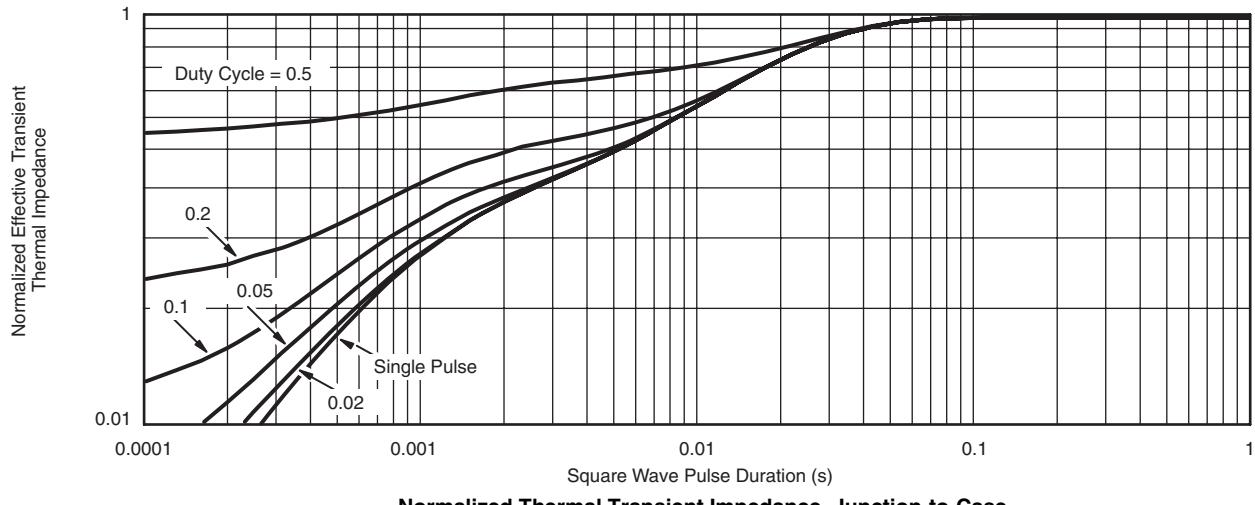
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power

* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

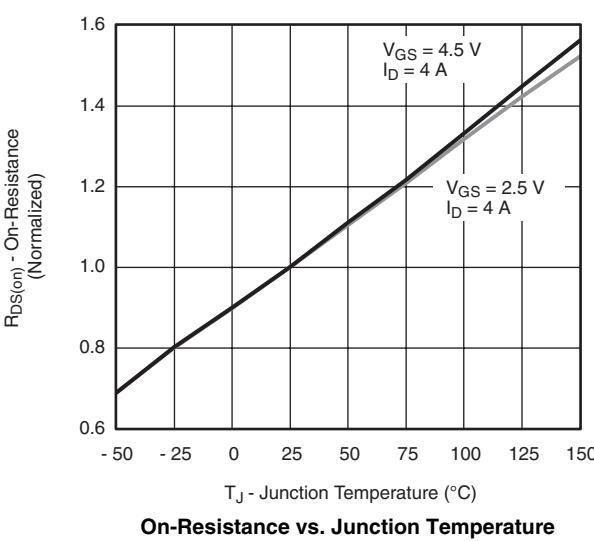
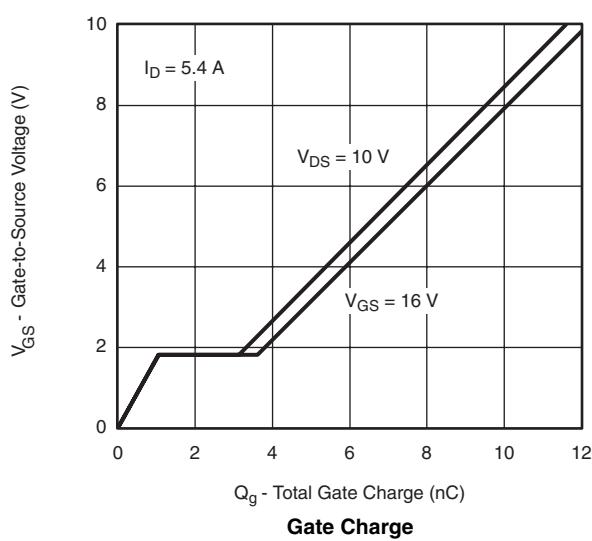
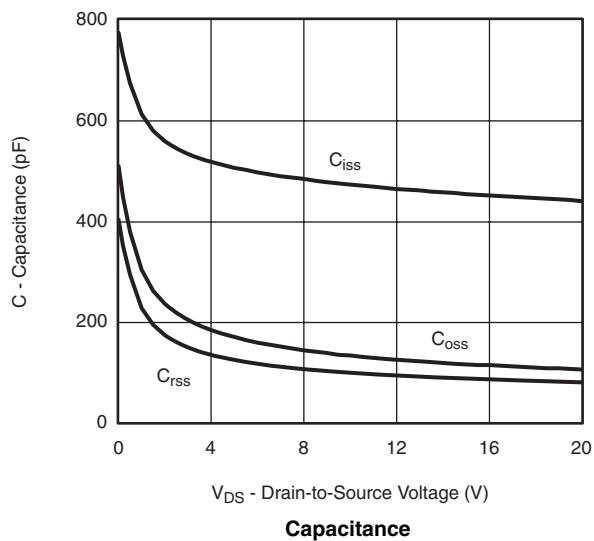
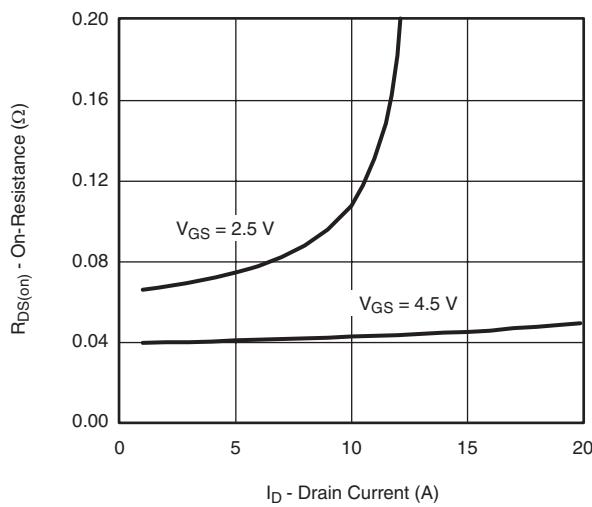
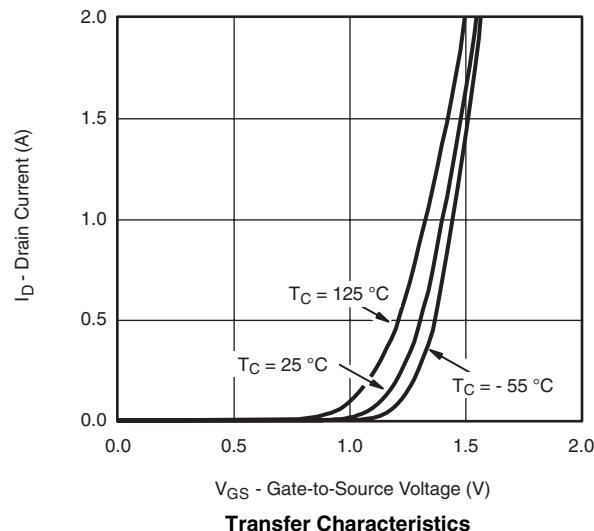
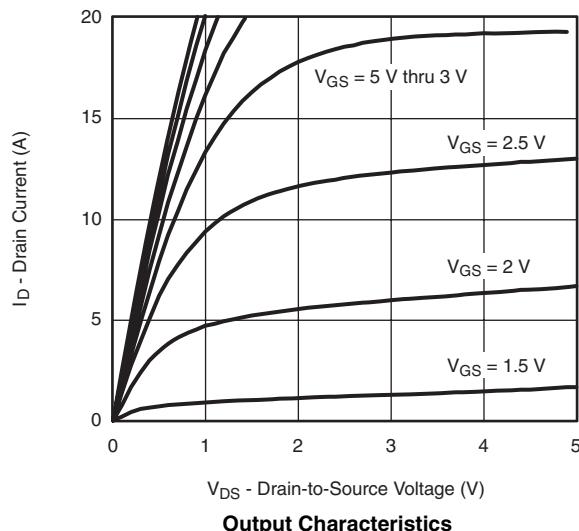
Safe Operating Area, Junction-to-Ambient

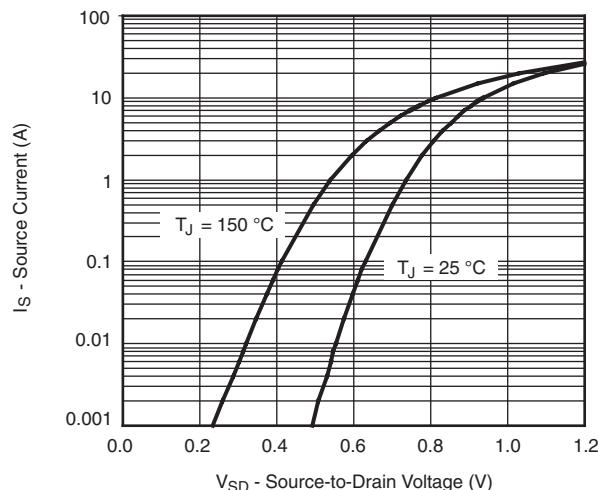
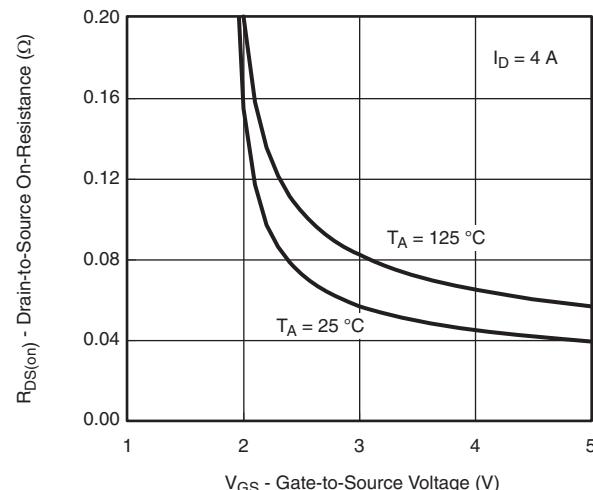
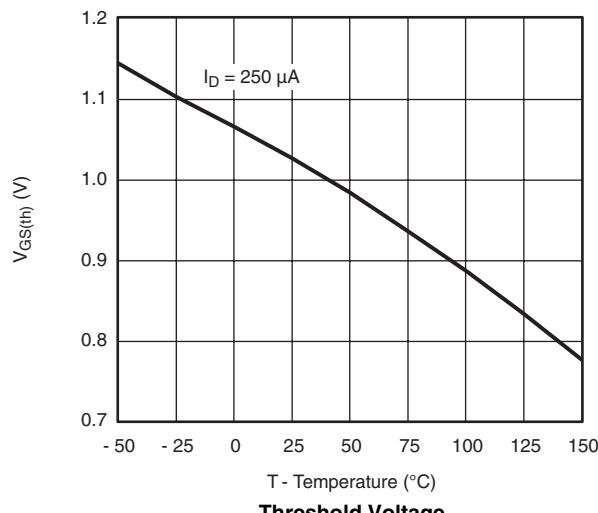
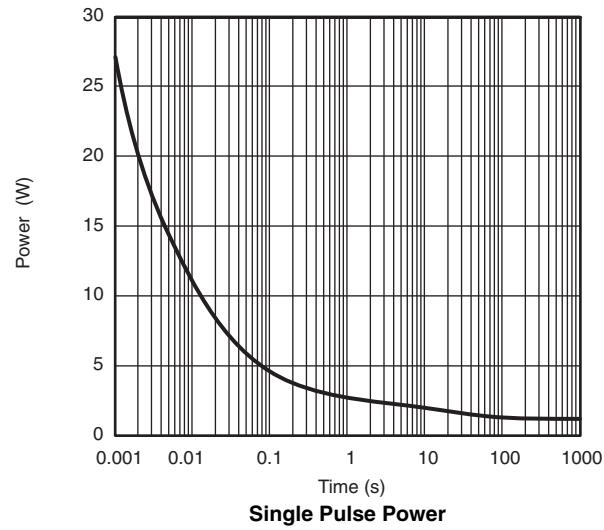
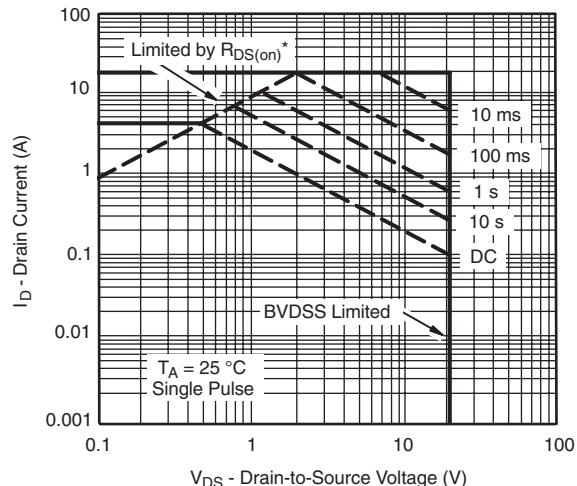
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

* The power dissipation P_D is based on $T_{J(\max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

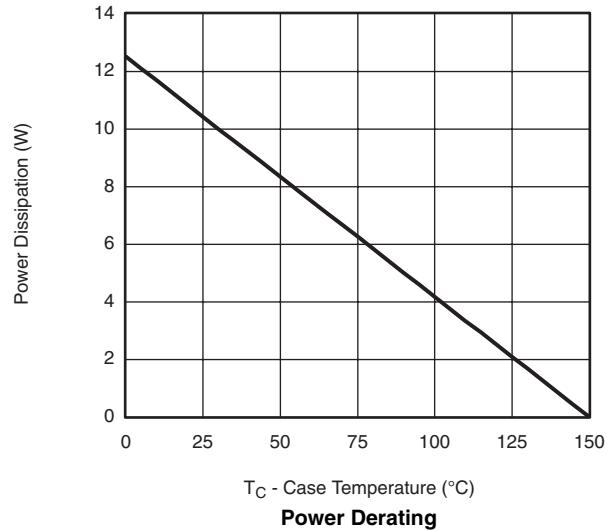
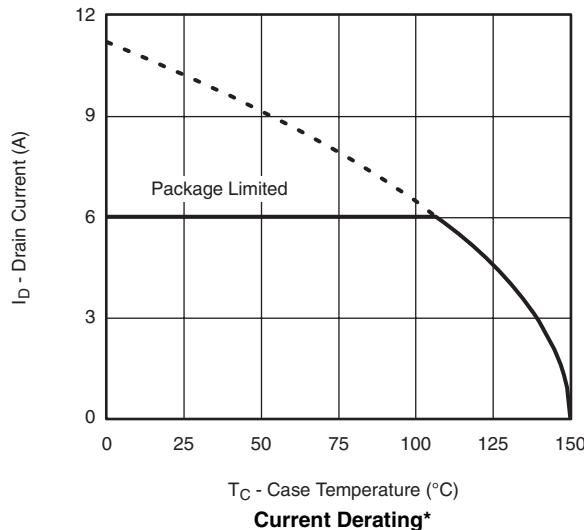
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

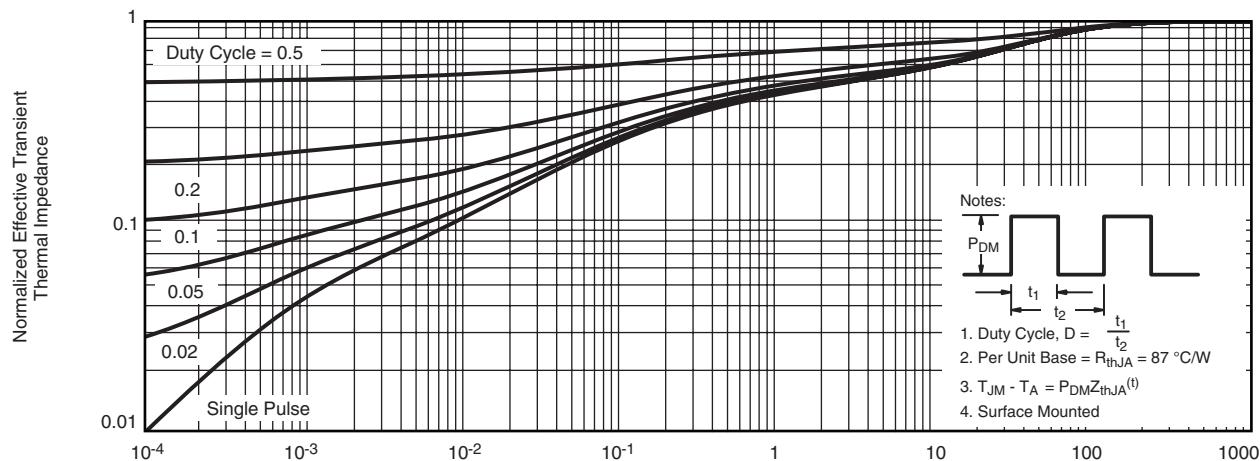
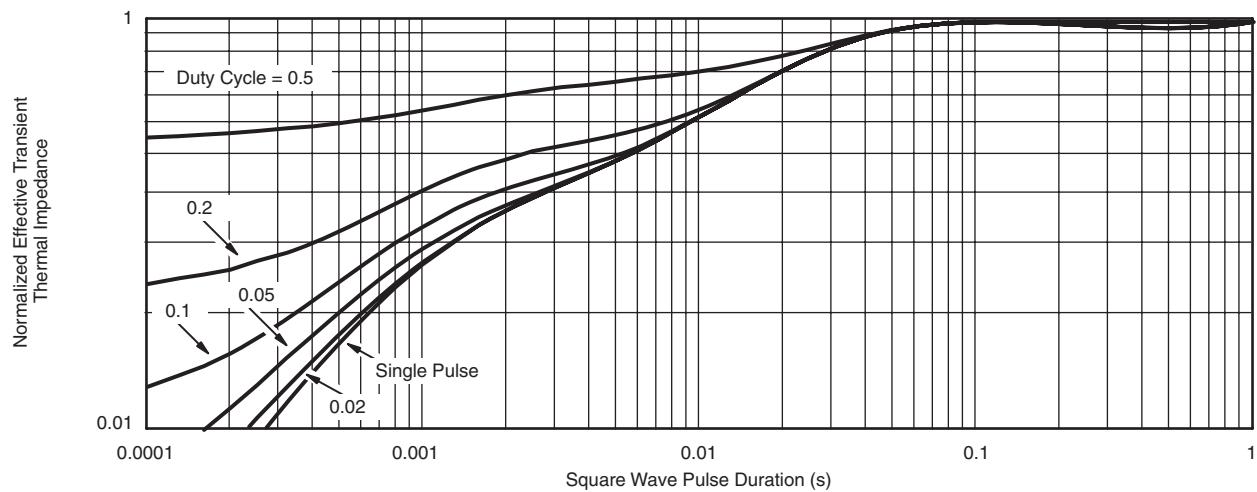


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Case

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

* The power dissipation P_D is based on $T_{J(\max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case

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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.